# **Bipolar Transistor**



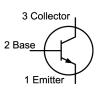


### **Description:**

The 2N3902 is a silicon NPN transistor in a TO-3 type Package designed for use in high voltage inverters, converters, switching regulators and line Operated amplifiers.

## RoHS Compliant

NPN



### **Maximum Ratings:**

Characteristic	Symbol	Rating	Unit		
Collector-Emitter Voltage	V <sub>CEX</sub>	700			
Collector-Emitter Voltage	V <sub>CEO(sus)</sub>	400	V		
Emitter Base Voltage	$V_{EB}$	5			
Collector Current -Continuous	I <sub>C</sub>	3.5	А		
Peak Base Current	I <sub>B</sub>	2			
Total Device Dissipation -(T <sub>C</sub> = +75°C), Derate Above 95°C	P <sub>D</sub>	100 1.33	W W/°C		
Operating Junction Temperature Range	T <sub>J</sub>	-65 to +150	°C		
Storage Temperature Range,	T <sub>stq</sub>	-65 to +200	]		
Thermal Resistance, Junction-to-Case	R <sub>thJC</sub>	0.75	°C/W		
Maximum Lead temperature (During Soldering, 1/8" from case, 5sec)	T <sub>L</sub>	+275	°C		

#### Electrical Characteristics: (T<sub>c</sub> = +25°C Unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Max	Unit		
OFF Characteristics (Note 2)							
Collector-Emitter Sustaining Voltage	V <sub>CEO(SUS)</sub>	I <sub>C</sub> = 100mA, I <sub>B</sub> = 0	325	-	V		
Collector Cutoff Current	I <sub>CEO</sub>	$V_{CE}^{}=400V, V_{BE}^{}=0$		0.25	mA		
Emitter-Base Voltage	lge $I_{EBO}$ $I_{E} = 100 \text{mA. } I_{C} = 5 \text{V}$		7 -	5	IIIA L		
ON Characteristics (Note 2)			,	,			
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 1A	30	90			
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	1 - 250 1 - 050		2.5	V		
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = 2.5 A, I_{\rm B} = 0.5 A$	_	2	V		
Dynamic Characteristics							
Current Gain-Bandwidth Product	f <sub>⊤</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 200mA, f = 1MHz	2.8	-	MHz		

#### Note:

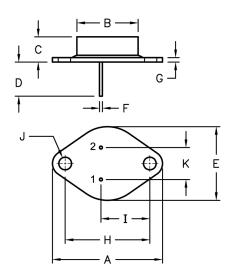
Pulse Test : Pulse Width = 5ms, Duty Cycle ≤10%
Pulse Test : Pulse Width = 300µs, Duty Cycle ≤2%

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#### Pin Configuration:

Pin 1. Base

Pin 2. Emitter

Collector (Case)

Dim	Α	В	С	D	E	F	G	Н	_	J	K
Min.	38.75	19.28	7.96	11.18	25.2	0.92	1.38	29.9	16.64	3.88	10.67
Max.	39.96	22.23	9.28	12.19	26.67	1.09	1.62	30.4	17.3	4.36	11.18

Dimensions: Millimetres

#### **Part Number Table**

Description	Part Number			
Transistor, NPN, 3.5A, 400V, TO-3	2N3902			

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